

SM120 THRU SM160

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SM120 THRU SM160

1.0A Surface Mount Schottky Barrier Rectifiers - 20V-60V

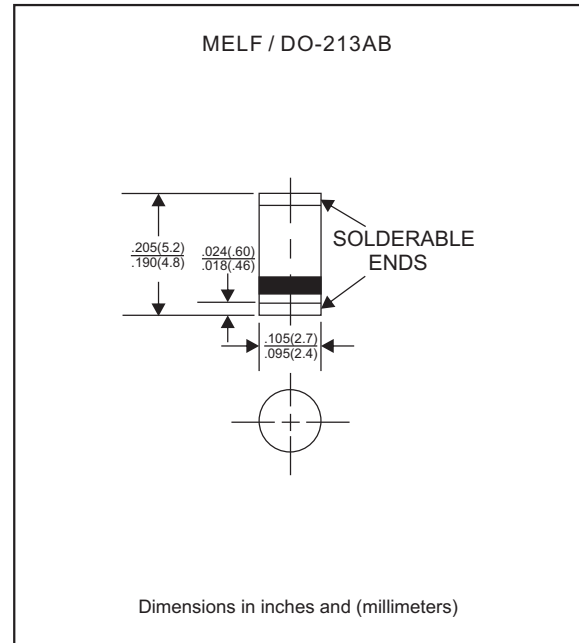
Features

- Low profile surface mounted application in order to optimize board space.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.
- Guardring for overvoltage protection.
- Ultra high-speed switching.
- Silicon epitaxial planar chip, metal silicon junction.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228
- Suffix "-H" indicates Halogen free parts, ex. SM120-H.

Mechanical data

- Epoxy : UL94-V0 rated flame retardant
- Case : Molded plastic, MELF / DO-213AB
- Terminals :Plated terminals, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.14 gram

Package outline



Maximum ratings and Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.1	I_O			1.0	A
Forward surge current	8.3ms single half sine-wave (JEDEC methode)	I_{FSM}			30	A
Reverse current	$V_R = V_{RRM} \quad T_J = 25^{\circ}\text{C}$	I_R			0.5	mA
	$V_R = V_{RRM} \quad T_J = 100^{\circ}\text{C}$				10	
Thermal resistance	Junction to ambient	$R_{\theta JA}$		50		$^{\circ}\text{C/W}$
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	C_J		110		pF
Storage temperature		T_{STG}	-65		+175	$^{\circ}\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	Operating temperature $T_J, (^{\circ}\text{C})$
SM120	20	14	20	0.50	-55 to +125
SM130	30	21	30		
SM140	40	28	40		
SM150	50	35	50	0.70	-55 to +150
SM160	60	42	60		

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage@ $I_F=1.0\text{A}$

Rating and characteristic curves (SM120 THRU SM160)

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

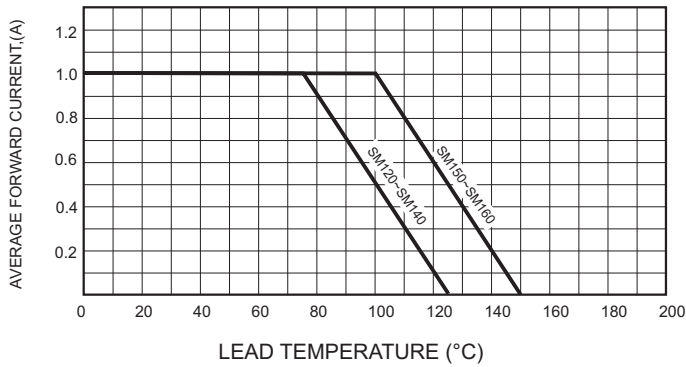


FIG.2-TYPICAL FORWARD CHARACTERISTICS

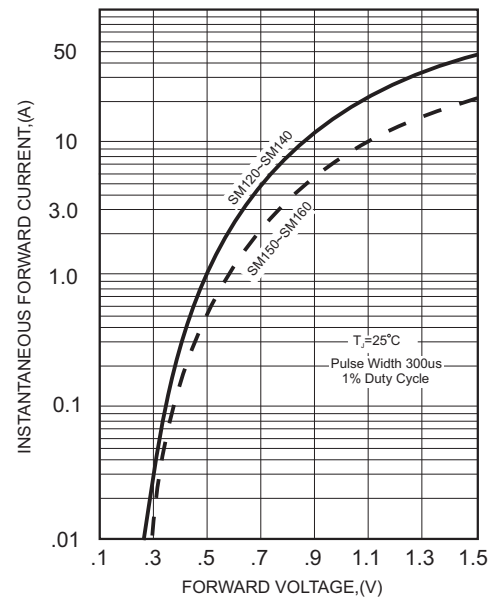


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

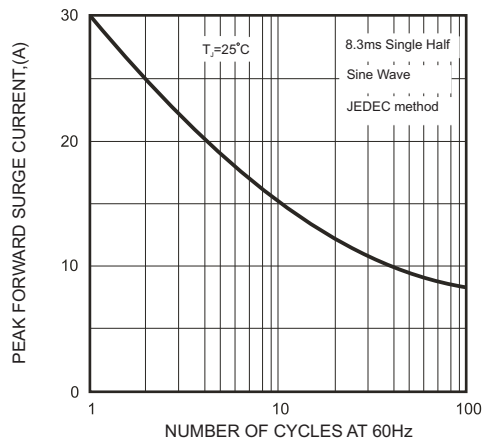


FIG.4-TYPICAL JUNCTION CAPACITANCE

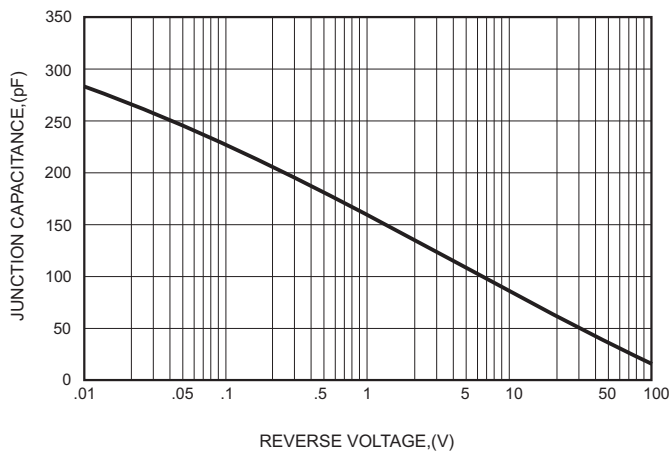
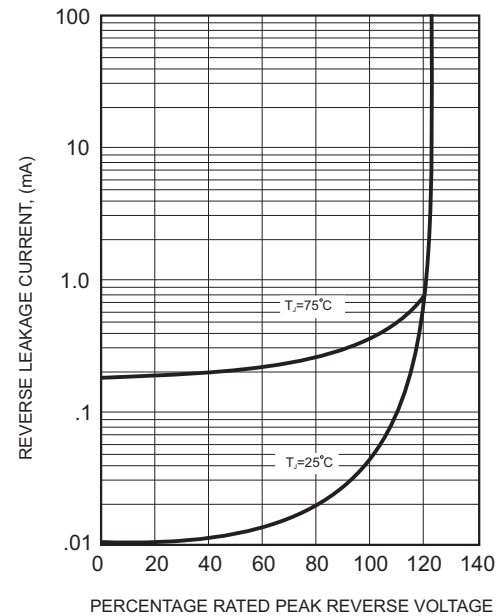


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



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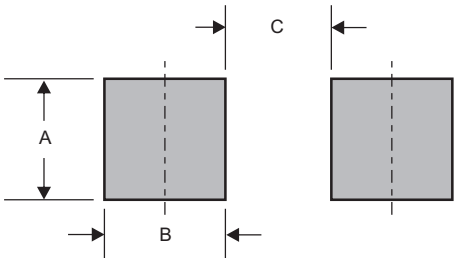
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
SM120	Cathode Only
SM130	Cathode Only
SM140	Cathode Only
SM150	Cathode Only
SM160	Cathode Only

Suggested solder pad layout

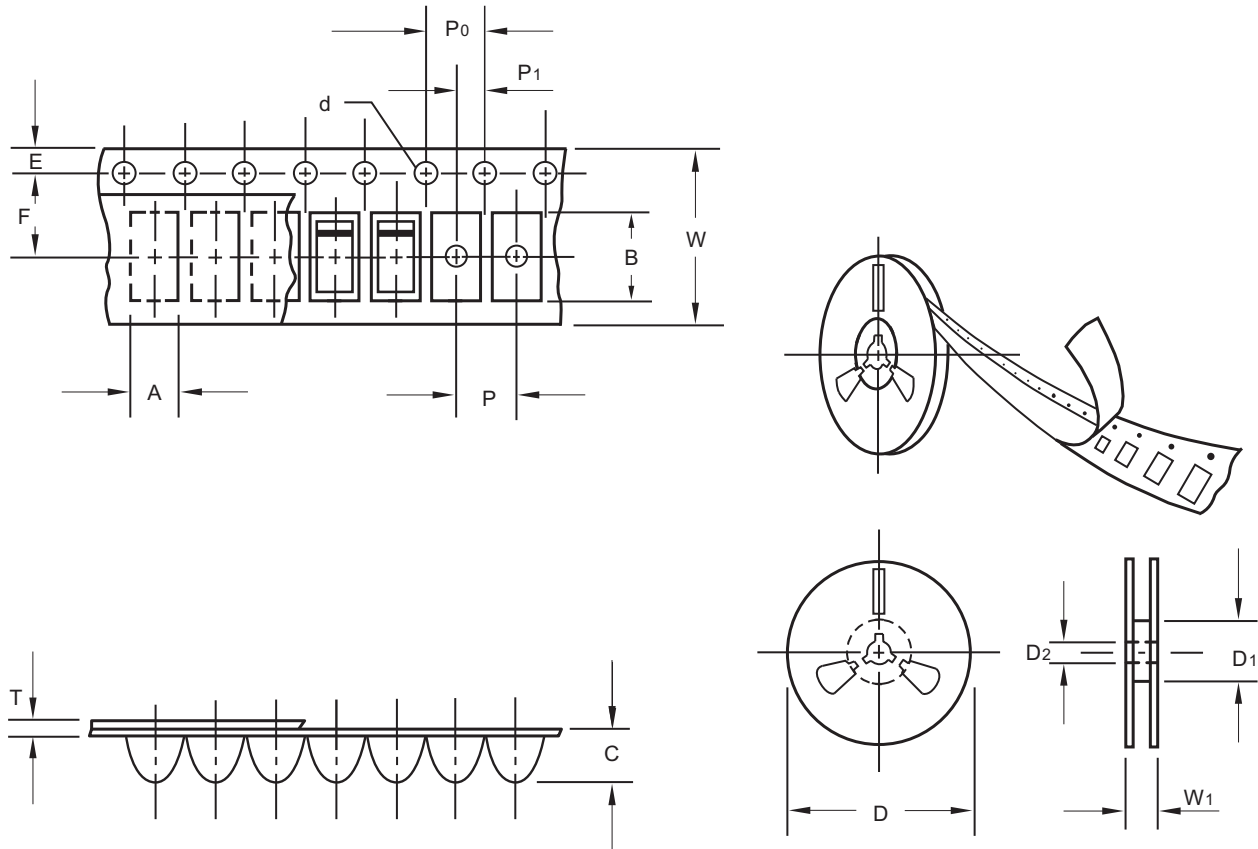


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
MELF / DO-213AB	0.118 (3.00)	0.079 (2.00)	0.130 (3.30)

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Packing information



unit:mm

Item	Symbol	Tolerance	MELF / DO-213AB
Carrier width	A	0.1	3.00
Carrier length	B	0.1	5.33
Carrier depth	C	0.1	3.00
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330
13" Reel inner diameter	D1	min	50
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	12.00
Reel width	W1	1.0	18.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

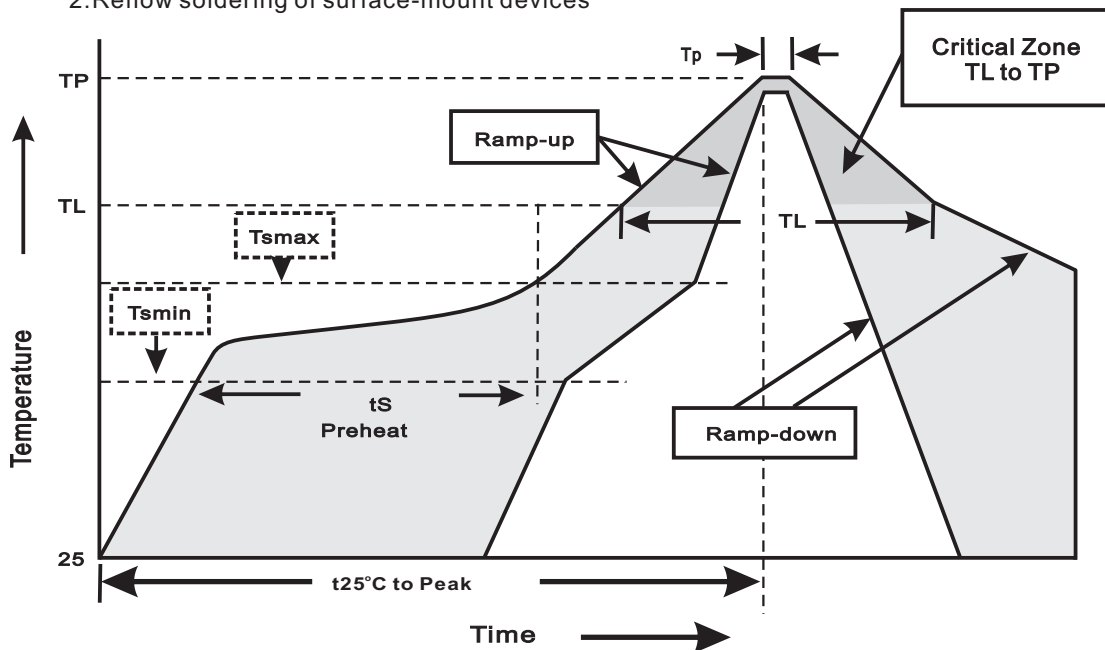
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
MELF / DO-213AB	13"	5,000	4.0	10,000	335*335*38	330	350*330*360	80,000	17.0

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	<3°C/sec
Preheat -Temperature Min(T_{smin}) -Temperature Max(T_{smax}) -Time(min to max)(t_s)	150°C 200°C 60~120sec
T_{smax} to T_L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T_L) -Time(t_L)	217°C 60~260sec
Peak Temperature(T_P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t_P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at $260 \pm 5^{\circ}\text{C}$ for $10 \pm 2\text{sec.}$	MIL-STD-750D METHOD-2031
2. Solderability	at $245 \pm 5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R = 80\%$ rate at $T_J = 125^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A = 25^{\circ}\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A = 121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	8.3ms single half sine-wave , one surge.	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A = 85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031